Preliminary Amendment

Applicant(s): Eugene P. Marsh

Serial No. Unknown (Parent Serial No. 09/146,866)

Filed: Herewith (Parent: 3 September 1998)

For: DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME

Remarks

Please enter the above amendment to the specification and consider the pending claims 23-39.

Conclusion

The Examiner is invited to contact Applicant's Representatives at the below-listed telephone number, if there are any questions regarding this Preliminary Amendment or if prosecution of this application may be assisted thereby.

Respectfully submitted,

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I hereby certify that this paper and/or fee is/are being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to the Assistant Commissioner for Patents, Attn: Box Patent Application, Washington, D. C.

APPENDIX A - SPECIFICATION AMENDMENTS INCLUDING NOTATIONS TO INDICATE CHANGES MADE

Serial No.: Unassigned Docket No.: 150.0064 0102

Amendments to the following are indicated by underlining what has been added and bracketing what has been deleted.

In the Specification

The paragraph beginning at page 10, line 13, has been amended as follows:

Any ruthenium-containing precursor and platinum-containing precursor may be used in accordance with the present invention. Preferably, the platinum containing precursors include MeCpPtMe₃ (where Cp=cyclopentadienyl), platinum hexafluoroacetylacetonate, CpPtMe₃, Pt(acetylacetonate)₂, Pt(PF₃)₄, Pt(CO)₂Cl₂, cis-PtMe₂[MeNC]₂, (COD)Pt(CH₃)₂, $(COD)Pt(CH_3)Cl$, $(C_5H_5)Pt(CH_3)(CO)$, $(acac)(Pt)(CH_3)_3$, where COD = 1,5 cycloctadiene and acac = acetylacetonate. Further, preferably, the ruthenium precursors are liquid ruthenium complexes of the following formula (Formula I): (diene)Ru(CO)₃ wherein: "diene" refers to linear, branched, or cyclic dienes, bicyclic dienes, tricyclic dienes, fluorinated derivatives thereof, combinations thereof, and derivatives thereof additionally containing heteroatoms such as halide, Si, S, Se, P, As, or N. These precursor complexes and others are described in Assignees' copending patent application entitled "Precursor Chemistries for Chemical Vapor Deposition of Ruthenium and Ruthenium Oxide" having U.S. [Serial No. _____ (Micron Docket No. 97-0675)] Serial No. 09/141,236, filed August 27, 1998 and in Assignees' copending patent application entitled "Methods for Preparing Ruthenium and Osmium Compounds" having U.S. [Serial No. _____ (Micron Docket No. 97-0861)] Serial No. 09/141,431, filed August 27, 1998. Further, for example, additional precursors are generally discussed in U.S. Patent No. 5,372,849 to McCormick et al. More preferably, the ruthenium precursors used according to the present invention include one of C₆H₈Ru(CO)₃, bis(cyclopentadienyl) ruthenium (II), triruthenium dodecacarbonyl, and cyclopentadienyl dicarbonyl ruthenium (II) dimer.

The paragraph beginning at page 11, line 6, has been amended as follows:

Methods of forming the co-deposited platinum:ruthenium alloy layer 14 are described in co-pending patent application entitled "Method for Producing Low Carbon/Oxygen Conductive

Amendment and Response - Appendix A

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Layers" [(Docket No. 150.00730101 (Micron Docket No. 97-0996)] having U.S. Serial No. 09/146,297, filed September 3, 1998. One skilled in the art will recognize that these methods and various other methods may be used to form the platinum:ruthenium alloy layer 14 according to the present invention.

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